

AV Etcher Etch Rates for 2015 - (Å/min.)

Films	PECVD Nitride-340	PECVD Oxide-340	Thermal Oxide	Low Stress Nitride	Regular Nitride	Resist 1813	Resist 1818	Resist NR71 1500P	Resist NR71 3000P	Bare Silicon Wafer	
Recipes										<i>PR mask</i>	<i>Al2O3 mask</i>
Nit1	2185	330	311	564		626	580	677	712	2518	2301
Nit2	1450	131	117	333		253	256	296	368	630	1525*
Nit3	983	39	37	98		116	100	107	145	442	881
Fastpoly	2066	148	110	316		430	445	477	488	6821*	7161*
Pjsnitd1	1365	448	405	890		706	800	737	830	4399	6424*
Slowpoly	608	28	33	45		102	91		143	1086	1240
Tyb-test	(312)	43	50	0		16	13	35	128	0	42*
Pjsoxide	109	250	196	53		63	41	58	160	25	71
O2-clean						1106	1345	1052	978		

Note: All etch rate tests were performed with a whole 4" wafer, after a 10 minute O₂-clean and a 5 minute chamber seasoning

*Resulting etched Si features show varying degrees of 'grass' or micro-masking.